

17.5V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 17.5V
- BV_{CES} > 50V
- I_C = 5A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} <45mV @ 500mA
- R_{SAT} = 50mΩ @ 5A for a Low Equivalent On-Resistance
- hFE Specified up to 20A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Top View

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0

Pin-Out

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

Applications

- · Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control

SOT223 B C C C C Top View

Device Symbol

Ordering Information (Note 4)

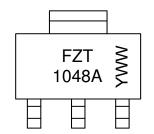
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1048ATA	FZT1048A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



FZT 1048A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	17.5	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	I _{CM}	20	Α
Base Current	l _Β	500	mA

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	В	2.0	W	
Power Dissipation	(Note 7)	P_{D}	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	В	62.5		
Thermal nesistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1		
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	10.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

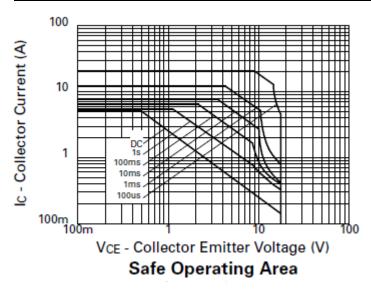
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

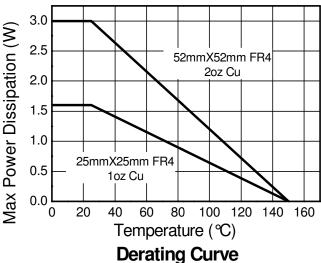
Notes:

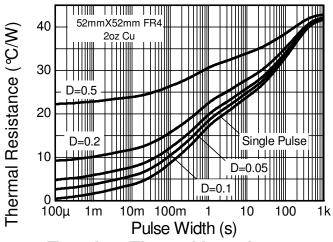
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

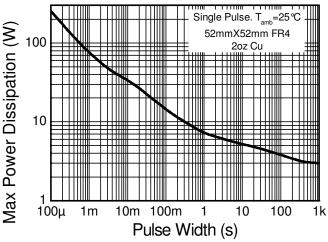


Thermal Characteristics and Derating Information





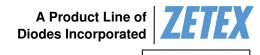




Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

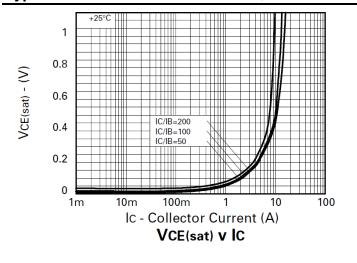
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	85	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	50	85	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEV}	50	85	_	V	$I_C = 100 \mu A, V_{EB} = 1 V$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	17.5	24	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.7	_	V	$I_E = 100\mu A$
Collector Cut-off Current	I _{CBO}	_	0.3	10	nA	V _{CB} = 35V
Collector Cut-off Current	Ices	_	0.3	10	nA	V _{CB} = 35V
Emitter Cut-off Current	I _{EBO}	_	0.3	10	nA	V _{EB} = 4V
		_	27	45	mV	I _C = 500mA, I _B = 10mA
Collector Emitter Seturation Voltage (Note 11)		_	55	75		I _C = 1A, I _B = 10mA
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	155	210		I _C = 3A, I _B = 15mA
		_	250	350		I _C = 5A, I _B = 25mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	920	1,000	mV	I _C = 5A, I _B = 25mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	880	970	mV	I _C = 5A, V _{CE} = 2V
		290	440	1,200		I _C = 10mA, V _{CE} = 2V
DC Commant Cain (Nata 11)	1-	300	450	1,200		I _C = 1A, V _{CE} = 2V
DC Current Gain (Note 11)	h _{FE}	180	300	_	_	I _C = 5A, V _{CE} = 2V
		50	90	_		I _C = 20A, V _{CE} = 2V
Output Capacitance	C _{obo}	_	60	80	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	_	150	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 50MHz
Cuitabing Times	t _{on}	_	120	_		I _C = 4A, V _{CC} = 10V,
Switching Times	t _{off}	_	310	_	ns	$I_{B1} = -I_{B2} = 40 \text{mA}$

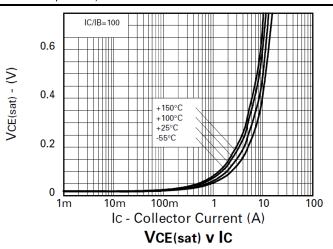
Note:

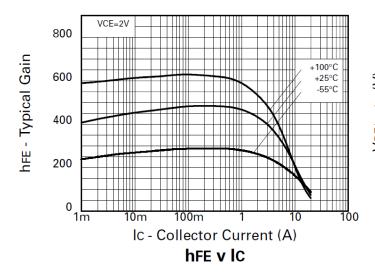
11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2.

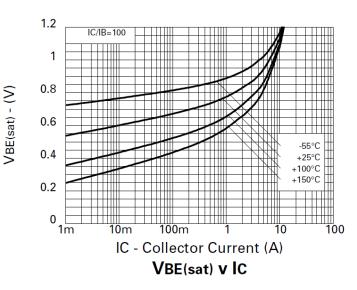


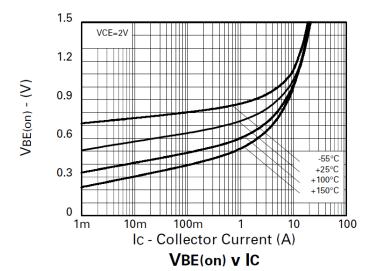
Typical Electrical Characteristics (@TA = +25 ℃, unless otherwise specified.)







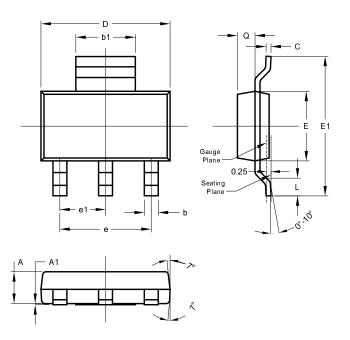






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

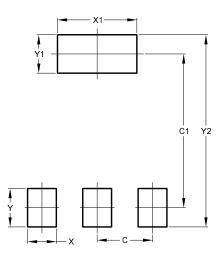


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
٦	0.85	1.05	0.95		
ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		





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